

# Pedram Khalili Amiri

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3132389/publications.pdf>

Version: 2024-02-01

143  
papers

7,133  
citations

57758

44  
h-index

60623

81  
g-index

144  
all docs

144  
docs citations

144  
times ranked

5016  
citing authors

#	ARTICLE	IF	CITATIONS
1	Switching of perpendicular magnetization by spin-orbit torques in the absence of external magnetic fields. <i>Nature Nanotechnology</i> , 2014, 9, 548-554.	31.5	753
2	Low-power non-volatile spintronic memory: STT-RAM and beyond. <i>Journal Physics D: Applied Physics</i> , 2013, 46, 074003.	2.8	391
3	Room-Temperature Creation and Spin-Orbit Torque Manipulation of Skyrmions in Thin Films with Engineered Asymmetry. <i>Nano Letters</i> , 2016, 16, 1981-1988.	9.1	275
4	Strong Rashba-Edelstein Effect-Induced Spin-Orbit Torques in Monolayer Transition Metal Dichalcogenide/Ferromagnet Bilayers. <i>Nano Letters</i> , 2016, 16, 7514-7520.	9.1	247
5	Voltage-Induced Ferromagnetic Resonance in Magnetic Tunnel Junctions. <i>Physical Review Letters</i> , 2012, 108, 197203.	7.8	231
6	Room-Temperature Skyrmion Shift Device for Memory Application. <i>Nano Letters</i> , 2017, 17, 261-268.	9.1	227
7	Ultra-low switching energy and scaling in electric-field-controlled nanoscale magnetic tunnel junctions with high resistance-area product. <i>Applied Physics Letters</i> , 2016, 108, .	3.3	186
8	Switching current reduction using perpendicular anisotropy in CoFe/MgO magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	169
9	Fast and programmable locomotion of hydrogel-metal hybrids under light and magnetic fields. <i>Science Robotics</i> , 2020, 5, .	17.6	163
10	Ultralow-current-density and bias-field-free spin-transfer nano-oscillator. <i>Scientific Reports</i> , 2013, 3, 1426.	3.3	162
11	Electrical control of reversible and permanent magnetization reorientation for magnetoelectric memory devices. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	153
12	Electric-field-induced spin wave generation using multiferroic magnetoelectric cells. <i>Applied Physics Letters</i> , 2014, 104, 082403.	3.3	144
13	High-Power Coherent Microwave Emission from Magnetic Tunnel Junction Nano-oscillators with Perpendicular Anisotropy. <i>ACS Nano</i> , 2012, 6, 6115-6121.	14.6	125
14	Giant spin-torque diode sensitivity in the absence of bias magnetic field. <i>Nature Communications</i> , 2016, 7, 11259.	12.8	123
15	VOLTAGE-CONTROLLED MAGNETIC ANISOTROPY IN SPINTRONIC DEVICES. <i>Spin</i> , 2012, 02, 1240002.	1.3	122
16	Magnetization switching through spin-Hall-effect-induced chiral domain wall propagation. <i>Physical Review B</i> , 2014, 89, .	3.2	121
17	Temperature dependence of the voltage-controlled perpendicular anisotropy in nanoscale MgO CoFeB Ta magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	119
18	Electric-Field-Controlled Magnetoelectric RAM: Progress, Challenges, and Scaling. <i>IEEE Transactions on Magnetics</i> , 2015, 51, 1-7.	2.1	108

#	ARTICLE	IF	CITATIONS
19	Field-free spin-orbit torque-induced switching of perpendicular magnetization in a ferrimagnetic layer with a vertical composition gradient. <i>Nature Communications</i> , 2021, 12, 4555.	12.8	105
20	Low writing energy and sub nanosecond spin torque transfer switching of in-plane magnetic tunnel junction for spin torque transfer random access memory. <i>Journal of Applied Physics</i> , 2011, 109, .	2.5	99
21	Room-Temperature Skyrmions in an Antiferromagnet-Based Heterostructure. <i>Nano Letters</i> , 2018, 18, 980-986.	9.1	98
22	Enhancement of voltage-controlled magnetic anisotropy through precise control of Mg insertion thickness at CoFeB MgO interface. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	92
23	Electric-field guiding of magnetic skyrmions. <i>Physical Review B</i> , 2015, 92, .	3.2	89
24	Deep subnanosecond spin torque switching in magnetic tunnel junctions with combined in-plane and perpendicular polarizers. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	82
25	Comparative Evaluation of Spin-Transfer-Torque and Magnetoelectric Random Access Memory. <i>IEEE Journal on Emerging and Selected Topics in Circuits and Systems</i> , 2016, 6, 134-145.	3.6	81
26	Magneto-optical investigation of spin-orbit torques in metallic and insulating magnetic heterostructures. <i>Nature Communications</i> , 2015, 6, 8958.	12.8	80
27	Giant voltage modulation of magnetic anisotropy in strained heavy metal/magnet/insulator heterostructures. <i>Physical Review B</i> , 2015, 92, .	3.2	79
28	Strain-induced modulation of perpendicular magnetic anisotropy in Ta/CoFeB/MgO structures investigated by ferromagnetic resonance. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	79
29	Giant interfacial perpendicular magnetic anisotropy in MgO/CoFe/capping layer structures. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	73
30	Current-driven perpendicular magnetization switching in Ta/CoFeB/[TaOx or MgO/TaOx] films with lateral structural asymmetry. <i>Applied Physics Letters</i> , 2014, 105, .	3.3	71
31	The promise of spintronics for unconventional computing. <i>Journal of Magnetism and Magnetic Materials</i> , 2021, 521, 167506.	2.3	66
32	Electrical manipulation of the magnetic order in antiferromagnetic PtMn pillars. <i>Nature Electronics</i> , 2020, 3, 92-98.	26.0	65
33	Voltage-induced switching of nanoscale magnetic tunnel junctions. , 2012, , .		59
34	Spin-orbit torques in perpendicularly magnetized Ir <sub>22</sub> Mn <sub>78</sub> /Co <sub>20</sub> Fe <sub>60</sub> B <sub>20</sub> /MgO multilayer. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	58
35	Effect of the oxide layer on current-induced spin-orbit torques in Hf CoFeB MgO and Hf CoFeB TaOx structures. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	55
36	Current-induced spin-orbit torque switching of perpendicularly magnetized Hf CoFeB MgO and Hf CoFeB TaOx structures. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	55

#	ARTICLE	IF	CITATIONS
37	Electric-Field Control of Spin-Orbit Interaction for Low-Power Spintronics. Proceedings of the IEEE, 2016, 104, 1974-2008.	21.3	53
38	4.7 A 65nm ReRAM-enabled nonvolatile processor with 6Å— reduction in restore time and 4Å— higher clock frequency using adaptive data retention and self-write-termination nonvolatile logic. , 2016, , .		53
39	Low Write-Energy Magnetic Tunnel Junctions for High-Speed Spin-Transfer-Torque MRAM. IEEE Electron Device Letters, 2011, 32, 57-59.	3.9	51
40	Magnetolectric Random Access Memory-Based Circuit Design by Using Voltage-Controlled Magnetic Anisotropy in Magnetic Tunnel Junctions. IEEE Nanotechnology Magazine, 2015, 14, 992-997.	2.0	50
41	Effect of resistance-area product on spin-transfer switching in MgO-based magnetic tunnel junction memory cells. Applied Physics Letters, 2011, 98, .	3.3	49
42	Experimental Demonstration of Spintronic Broadband Microwave Detectors and Their Capability for Powering Nanodevices. Physical Review Applied, 2019, 11, .	3.8	49
43	Nanoscale magnetic tunnel junction sensors with perpendicular anisotropy sensing layer. Applied Physics Letters, 2012, 101, 062412.	3.3	48
44	Electric-field-driven magnetization switching and nonlinear magnetoelasticity in Au/FeCo/MgO heterostructures. Scientific Reports, 2016, 6, 29815.	3.3	48
45	Joule Heating Effect on Field-Free Magnetization Switching by Spin-Orbit Torque in Exchange-Biased Systems. Physical Review Applied, 2017, 7, .	3.8	48
46	Thermally stable voltage-controlled perpendicular magnetic anisotropy in Mo   CoFeB   MgO structures. Applied Physics Letters, 2015, 107, .	3.3	47
47	Sub-200Åps spin transfer torque switching in in-plane magnetic tunnel junctions with interface perpendicular anisotropy. Journal Physics D: Applied Physics, 2012, 45, 025001.	2.8	46
48	Ultrahigh detection sensitivity exceeding 105 V/W in spin-torque diode. Applied Physics Letters, 2018, 113, .	3.3	43
49	Nonreciprocal spin wave spectroscopy of thin Niâ€Fe stripes. Applied Physics Letters, 2007, 91, .	3.3	42
50	Electric field control and effect of Pd capping on magnetocrystalline anisotropy in FePd thin films: A first-principles study. Physical Review B, 2014, 89, .	3.2	41
51	A ReRAM-Based Nonvolatile Flip-Flop With Self-Write-Termination Scheme for Frequent-OFF Fast-Wake-Up Nonvolatile Processors. IEEE Journal of Solid-State Circuits, 2017, 52, 2194-2207.	5.4	41
52	Enhancement of microwave emission in magnetic tunnel junction oscillators through in-plane field orientation. Applied Physics Letters, 2011, 99, .	3.3	39
53	Diode-MTJ Crossbar Memory Cell Using Voltage-Induced Unipolar Switching for High-Density MRAM. IEEE Electron Device Letters, 2013, 34, 753-755.	3.9	39
54	Write Error Rate and Read Disturbance in Electric-Field-Controlled Magnetic Random-Access Memory. IEEE Magnetics Letters, 2017, 8, 1-5.	1.1	37

#	ARTICLE	IF	CITATIONS
55	Spin-torque ferromagnetic resonance measurements utilizing spin Hall magnetoresistance in W/Co40Fe40B20/MgO structures. Applied Physics Letters, 2016, 109, .	3.3	36
56	Strain-mediated 180° perpendicular magnetization switching of a single domain multiferroic structure. Journal of Applied Physics, 2015, 118, 014101.	2.5	35
57	Effect of heavy metal layer thickness on spin-orbit torque and current-induced switching in Hf CoFeB MgO structures. Applied Physics Letters, 2016, 109, .	3.3	33
58	Dynamics of domain-wall motion driven by spin-orbit torque in antiferromagnets. Physical Review B, 2020, 101, .	3.2	33
59	Enhanced voltage-controlled magnetic anisotropy in magnetic tunnel junctions with an MgO/PZT/MgO tunnel barrier. Applied Physics Letters, 2016, 108, .	3.3	32
60	Design of high-throughput and low-power true random number generator utilizing perpendicularly magnetized voltage-controlled magnetic tunnel junction. AIP Advances, 2017, 7, .	1.3	31
61	Observation of current-induced switching in non-collinear antiferromagnetic IrMn3 by differential voltage measurements. Nature Communications, 2021, 12, 3828.	12.8	31
62	Control of Spin-Wave Damping in YIG Using Spin Currents from Topological Insulators. Physical Review Applied, 2019, 11, .	3.8	30
63	Reduction of switching current density in perpendicular magnetic tunnel junctions by tuning the anisotropy of the CoFeB free layer. Journal of Applied Physics, 2012, 111, 07C907.	2.5	28
64	Magneto-electric tuning of the phase of propagating spin waves. Applied Physics Letters, 2012, 101, .	3.3	28
65	Electric-field-induced thermally assisted switching of monodomain magnetic bits. Journal of Applied Physics, 2013, 113, .	2.5	27
66	Analysis and Compact Modeling of Magnetic Tunnel Junctions Utilizing Voltage-Controlled Magnetic Anisotropy. IEEE Transactions on Magnetics, 2018, 54, 1-9.	2.1	27
67	In-plane current-driven spin-orbit torque switching in perpendicularly magnetized films with enhanced thermal tolerance. Applied Physics Letters, 2016, 108, .	3.3	26
68	Spin-Torque Driven Switching Probability Density Function Asymmetry. IEEE Transactions on Magnetics, 2012, 48, 3818-3820.	2.1	24
69	Colossal electric field control of magnetic anisotropy at ferromagnetic interfaces induced by iridium overlayers. Physical Review B, 2019, 99, .	3.2	24
70	Spin-Torque Ferromagnetic Resonance in $W/Co_{1-x}Fe_xB_{20}MgO$ Structures. Applied Physics Letters, 2016, 109, .	3.3	23
71	Perpendicular magnetization switching by large spin-orbit torques from sputtered $Bi_{2-x}Te_{3-x}$ . Chinese Physics B, 2020, 29, 078505.	1.4	23
72	Efficient Excitation of High-Frequency Exchange-Dominated Spin Waves in Periodic Ferromagnetic Structures. Physical Review Applied, 2017, 7, .	3.8	22

#	ARTICLE	IF	CITATIONS
73	Predictive Materials Design of Magnetic Random-Access Memory Based on Nanoscale Atomic Structure and Element Distribution. <i>Nano Letters</i> , 2019, 19, 8621-8629.	9.1	22
74	Voltage-Controlled Magnetic Anisotropy in Heterostructures with Atomically Thin Heavy Metals. <i>Physical Review Applied</i> , 2019, 12, .	3.8	22
75	Competing effect of spin-orbit torque terms on perpendicular magnetization switching in structures with multiple inversion asymmetries. <i>Scientific Reports</i> , 2016, 6, 23956.	3.3	21
76	Perpendicular magnetic tunnel junction with W seed and capping layers. <i>Journal of Applied Physics</i> , 2017, 121, .	2.5	21
77	Spin wave functions nanofabric update. , 2011, , .		20
78	Effects of annealing on the magnetic properties and microstructures of Ta/Mo/CoFeB/MgO/Ta films. <i>Journal of Alloys and Compounds</i> , 2017, 692, 243-248.	5.5	20
79	Picosecond Electric-Field-Induced Switching of Antiferromagnets. <i>Physical Review Applied</i> , 2019, 11, .	3.8	20
80	In-plane magnetic field effect on switching voltage and thermal stability in electric-field-controlled perpendicular magnetic tunnel junctions. <i>AIP Advances</i> , 2016, 6, 075014.	1.3	19
81	Strain control magnetocrystalline anisotropy of Ta/FeCo/MgO heterostructures. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	18
82	Design of a Fast and Low-Power Sense Amplifier and Writing Circuit for High-Speed MRAM. <i>IEEE Transactions on Magnetics</i> , 2015, 51, 1-7.	2.1	18
83	A ReRAM-based single-NVM nonvolatile flip-flop with reduced stress-time and write-power against wide distribution in write-time by using self-write-termination scheme for nonvolatile processors in IoT era. , 2016, , .		17
84	Enhanced Broad-band Radio Frequency Detection in Nanoscale Magnetic Tunnel Junction by Interface Engineering. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 29382-29387.	8.0	17
85	Low-Power, High-Density Spintronic Programmable Logic With Voltage-Gated Spin Hall Effect in Magnetic Tunnel Junctions. <i>IEEE Magnetics Letters</i> , 2016, 7, 1-5.	1.1	16
86	Analog to Stochastic Bit Stream Converter Utilizing Voltage-Assisted Spin Hall Effect. <i>IEEE Electron Device Letters</i> , 2017, 38, 1343-1346.	3.9	16
87	Large voltage-controlled magnetic anisotropy in the SrTiO <sub>3</sub> /Fe/Cu structure. <i>Applied Physics Letters</i> , 2017, 111, 152403.	3.3	16
88	A Word Line Pulse Circuit Technique for Reliable Magnetoelectric Random Access Memory. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2017, 25, 2027-2034.	3.1	15
89	A Spintronic Voltage-Controlled Stochastic Oscillator for Event-Driven Random Sampling. <i>IEEE Electron Device Letters</i> , 2017, 38, 281-284.	3.9	15
90	Quantum computers. <i>IEEE Potentials</i> , 2002, 21, 6-9.	0.3	14

#	ARTICLE	IF	CITATIONS
91	Partial spin absorption induced magnetization switching and its voltage-assisted improvement in an asymmetrical all spin logic device at the mesoscopic scale. Applied Physics Letters, 2017, 111, .	3.3	14
92	MTJ variation monitor-assisted adaptive MRAM write. , 2016, , .		13
93	The computer chip that never forgets. IEEE Spectrum, 2015, 52, 30-56.	0.7	12
94	Source Line Sensing in Magneto-Electric Random-Access Memory to Reduce Read Disturbance and Improve Sensing Margin. IEEE Magnetism Letters, 2016, 7, 1-5.	1.1	11
95	Implementation of Artificial Neural Networks Using Magnetoresistive Random-Access Memory-Based Stochastic Computing Units. IEEE Magnetism Letters, 2021, 12, 1-5.	1.1	11
96	Deviation from exponential decay for spin waves excited with a coplanar waveguide antenna. Applied Physics Letters, 2012, 101, 252409.	3.3	10
97	Hybrid VC-MTJ/CMOS non-volatile stochastic logic for efficient computing. , 2017, , .		10
98	Anomalous Thermal-Assisted Spin-Orbit Torque-Induced Magnetization Switching for Energy-Efficient Logic-in-Memory. ACS Nano, 2022, 16, 8264-8272.	14.6	9
99	Spin-Transfer Torque Switching Above Ambient Temperature. IEEE Magnetism Letters, 2012, 3, 3000304-3000304.	1.1	8
100	Influence of inserted Mo layer on the thermal stability of perpendicularly magnetized Ta/Mo/Co <sub>20</sub> Fe <sub>60</sub> B <sub>20</sub> /MgO/Ta films. AIP Advances, 2016, 6, .	1.3	8
101	A 65-nm ReRAM-Enabled Nonvolatile Processor With Time-Space Domain Adaption and Self-Write-Termination Achieving $\times 4$ Faster Clock Frequency and $\times 6$ Higher Restore Speed. IEEE Journal of Solid-State Circuits, 2017, 52, 2769-2785.	5.4	8
102	The impact of Hf layer thickness on the perpendicular magnetic anisotropy in Hf/CoFeB/MgO/Ta films. Journal of Alloys and Compounds, 2017, 694, 76-81.	5.5	8
103	Adaptive MRAM Write and Read with MTJ Variation Monitor. IEEE Transactions on Emerging Topics in Computing, 2021, 9, 402-413.	4.6	8
104	3D Ferrimagnetic Device for Multi-Bit Storage and Efficient In-Memory Computing. IEEE Electron Device Letters, 2021, 42, 152-155.	3.9	8
105	Thermal stability characterization of magnetic tunnel junctions using hard-axis magnetoresistance measurements. Journal of Applied Physics, 2011, 109, 07C708.	2.5	7
106	Low-power MRAM for nonvolatile electronics: Electric field control and spin-orbit torques. , 2014, , .		7
107	Experimental Determination of the Nonuniform Shape-Induced Anisotropy Field in Thin $\text{Ni}/\text{Fe}$ Films. IEEE Transactions on Magnetism, 2007, 43, 1880-1883.	2.1	6
108	Quantitative analysis of electric field induced change in anisotropy field in $\text{Co}_{60}\text{Fe}_{20}\text{B}_{20}/(011)\text{xPb}(\text{Mg}_{1/3}\text{Nb}_{2/3})\text{O}_3-(1-x)\text{PbTiO}_3$ ( $x \approx 0.68$ ) heterostructures. Applied Physics Letters, 2012, 101, .	3.3	6

#	ARTICLE	IF	CITATIONS
109	Electric field induced domain-wall dynamics: Depinning and chirality switching. <i>Physical Review B</i> , 2013, 88, .	3.2	6
110	Oscillatory magnetic anisotropy and spin-reorientation induced by heavy-metal cap in Cu/FeCo/ M () Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5	3.2	6
111	Leveraging nMOS Negative Differential Resistance for Low Power, High Reliability Magnetic Memory. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 4084-4090.	3.0	6
112	High Frequency Extended Short-Wavelength Infrared Heterojunction Photodetectors Based on InAs/GaSb/AlSb Type-II Superlattices. <i>IEEE Journal of Quantum Electronics</i> , 2018, 54, 1-5.	1.9	6
113	Domain periodicity in an easy-plane antiferromagnet with Dzyaloshinskii-Moriya interaction. <i>Physical Review B</i> , 2020, 102, .	3.2	6
114	Antiferromagnetic Parametric Resonance Driven by Voltage-Controlled Magnetic Anisotropy. <i>Physical Review Applied</i> , 2022, 17, .	3.8	6
115	Nonreciprocal Spin Waves in Co-Ta-Zr Films and Multilayers. <i>IEEE Transactions on Magnetics</i> , 2009, 45, 4215-4218.	2.1	5
116	Magnetic bit stability: Competition between domain-wall and monodomain switching. <i>Applied Physics Letters</i> , 2012, 100, 212406.	3.3	5
117	The influence of an MgO nanolayer on the planar Hall effect in NiFe films. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	5
118	A Dual-Data Line Read Scheme for High-Speed Low-Energy Resistive Nonvolatile Memories. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2018, 26, 272-279.	3.1	5
119	Magnetostatic waves in layered materials and devices. <i>Journal of Applied Physics</i> , 2006, 100, 103909.	2.5	4
120	Integrated Microstrip Lines With Coâ€“Taâ€“Zr Magnetic Films. <i>IEEE Transactions on Magnetics</i> , 2008, 44, 3103-3106.	2.1	4
121	The influence of in-plane ferroelectric crystal orientation on electrical modulation of magnetic properties in Co <sub>60</sub> Fe <sub>20</sub> B <sub>20</sub> /SiO <sub>2</sub> /(011) xPb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> -(1â€“x)PbTiO <sub>3</sub> heterostructures. <i>Journal of Applied Physics</i> , 2012, 112, 033916.	2.5	4
122	Microstrip Array Ring FETs with 2D p-Ga <sub>2</sub> O <sub>3</sub> Channels Grown by MOCVD. <i>Photonics</i> , 2021, 8, 578.	2.0	4
123	Micromagnetic Investigation of a Voltage-Controlled Skyrmionic Magnon Switch. <i>Physical Review Applied</i> , 2022, 17, .	3.8	4
124	Ferromagnetic Thin Films for Loss Reduction in On-Chip Transmission Lines. <i>IEEE Transactions on Magnetics</i> , 2007, 43, 2630-2632.	2.1	3
125	Array-Level Analysis of Magneto-Electric Random-Access Memory for High-Performance Embedded Applications. <i>IEEE Magnetics Letters</i> , 2017, 8, 1-5.	1.1	3
126	Spin torques join forces in a memory device. <i>Nature Electronics</i> , 2018, 1, 576-577.	26.0	3



#	ARTICLE	IF	CITATIONS
127	Tight-Binding Analysis of Coupled Dielectric Waveguide Structures. Fiber and Integrated Optics, 2006, 25, 11-27.	2.5	2
128	High-resistivity nanogranular CoAlO films for high-frequency applications. Journal of Applied Physics, 2007, 101, 09M508.	2.5	2
129	Electric-field-controlled MRAM based on voltage control of magnetic anisotropy (VCMA): Recent progress and perspectives. , 2015, , .		2
130	Magnetic Tunnel Junctions and Their Applications in Nonvolatile Circuits. , 2015, , 1-36.		2
131	Ultra-low-power, high-density spintronic programmable logic (SPL). , 2016, , .		2
132	A model reduction based approach for extracting the diffusion and generation terms of pn junction leakage current. Semiconductor Science and Technology, 2003, 18, 234-240.	2.0	1
133	Ultrafast spin torque memory based on magnetic tunnel junctions with combined in-plane and perpendicular polarizers. , 2012, , .		1
134	A 3 pJ/bit free space optical interlink platform for self-powered tetherless sensing and opto-spintronic RF-to-optical transduction. Scientific Reports, 2021, 11, 8504.	3.3	1
135	Ultralow-current-density and bias-field-free spin-transfer nano-oscillator. , 0, .		1
136	On science, politics and simulations. IEEE Potentials, 2005, 24, 6-8.	0.3	0
137	GUEST EDITORIAL "RECENT PROGRESS IN SPINTRONIC DEVICES. Spin, 2012, 02, 1202001.	1.3	0
138	Spintronics for instant-on nonvolatile electronics. , 2012, , .		0
139	Size reduction and dual mode degeneracy in microstrip patch antenna using periodically rippled silicon substrate. , 2015, , .		0
140	Electric Control of Magnetic Devices for Spintronic Computing. , 2015, , 53-112.		0
141	Electric-field-controlled MRAM using voltage control of magnetic anisotropy: Progress, scaling, and challenges. , 2015, , .		0
142	Magnetic Tunnel Junctions and Their Applications in Non-volatile Circuits. , 2016, , 1127-1171.		0
143	Editorial for the Special Issue on Emerging Memory and Computing Devices in the Era of Intelligent Machines. Micromachines, 2020, 11, 73.	2.9	0